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Patent
Attorney's Docket No. 015290-502

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)	BOX AF
)	
Helen H. ZHU et al.)	Group Art Unit: 2823
)	
Application No.: 09/820,694)	Examiner: J. J. Maldonado
)	
Filed: March 30, 2001)	Confirmation No.: 7374
)	
For: METHOD OF PLASMA ETCHING)	
SILICON NITRIDE)	

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AMENDMENT/REPLY TRANSMITTAL LETTER

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Enclosed is a reply for the above-identified patent application.

- ☐ A Petition for Extension of Time is also enclosed.
- ☐ A Terminal Disclaimer and the ☐ \$55.00 (2814) ☐ \$110.00 (1814) fee due under 37 C.F.R. § 1.20(d) are also enclosed.
- ☐ Also enclosed is/are _____.
- ☐ Small entity status is hereby claimed.
- ☐ Applicant(s) request continued examination under 37 C.F.R. § 1.114 and enclose the ☐ \$375.00 (2801) ☐ \$750.00 (1801) fee due under 37 C.F.R. § 1.17(e).
- ☐ Applicant(s) previously submitted ___, on ___, for which continued examination is requested.
- ☐ Applicant(s) request suspension of action by the Office until at least ___, which does not exceed three months from the filing of this RCE, in accordance with 37 C.F.R. § 1.103(c). The required fee under 37 C.F.R. § 1.17(i) is enclosed.
- ☐ A Request for Entry and Consideration of Submission under 37 C.F.R. § 1.129(a) (1809/2809) is also enclosed.
- ☒ No additional claim fee is required.

☐ An additional claim fee is required, and is calculated as shown below:

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims		MINUS =		× \$18.00 (1202) =	
Independent Claims		MINUS =		× \$84.00 (1201) =	
If Amendment adds multiple dependent claims, add \$280.00 (1203)					
Total Amendment Fee					
If small entity status is claimed, subtract 50% of Total Amendment Fee					
TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT					

☐ A claim fee in the amount of \$_____ is enclosed.

☐ Charge \$_____ to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By:


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Date: March 4, 2003



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AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Final Official Action dated December 4, 2002, please amend the present application as follows.

IN THE CLAIMS:

A marked-up version of the claims showing insertions and deletions appears in Appendix A. Please rewrite Claim 1 as follows:

1. (Amended) A process for etching a silicon nitride layer with selectivity to an underlying and/or overlying dielectric layer, comprising:

introducing a semiconductor substrate into a medium density plasma etching reactor, the semiconductor substrate having a layer of silicon nitride and the layer of silicon nitride having an underlying and/or overlying dielectric layer;

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